

1.Description

The 40N06 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

2.2Features

- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

2.1Features

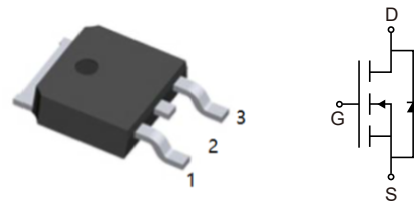
- $V_{DS(V)}=60V$
- $I_D=40A$
- $R_{DS(ON)}<14m\Omega(V_{GS}=10V)$
- $R_{DS(ON)}<16m\Omega(V_{GS}=4.5V)$

- Lead free product is acquired

3.Pinning information

Pin	Symbol	Description
1	G	GATE
3	S	SOURCE
2	D	DRAIN

TO-252(DPAK)
top view



4.Absolute Maximum Ratings $T_A=25^{\circ}C$

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Drain Current-Continuous ^{Note3}	$T_C=25^{\circ}C$	I_D	40	A
	$T_C=100^{\circ}C$		29	
Drain Current-Pulsed ^{Note1}		I_{DM}	160	
Avalanche Energy ^{Note4}		E_{AS}	64	mJ
Maximum Power Dissipation	$T_C=25^{\circ}C$	P_D	75	W
Storage Temperature Range		T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range		T_J	-55 to 150	$^{\circ}C$



5. Thermal resistance rating

Parameter	Symbol	Typ	Max	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$		1.4	°C/W

6. SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTIC						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =30A		14	18	mΩ
		V _{GS} =4.5V, I _{DS} =20A		16	22	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz		2928		pF
Output Capacitance	C _{oss}			141		pF
Reverse Transfer Capacitance	C _{rss}			120		pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =30V R _{GEN} =1.8Ω, I _D =25A		7.5		ns
Rise Time	t _r			6		ns
Turn-Off Delay Time	t _{D(off)}			28.4		ns
Fall Time	t _f			5.5		ns
Total Gate Charge at 10V	Q _g	V _{DS} =30V, I _{DS} =25A, V _{GS} =10V		50		nC
Gate to Source Gate Charge	Q _{gs}			6		nC
Gate to Drain“Miller”Charge	Q _{gd}			15		nC



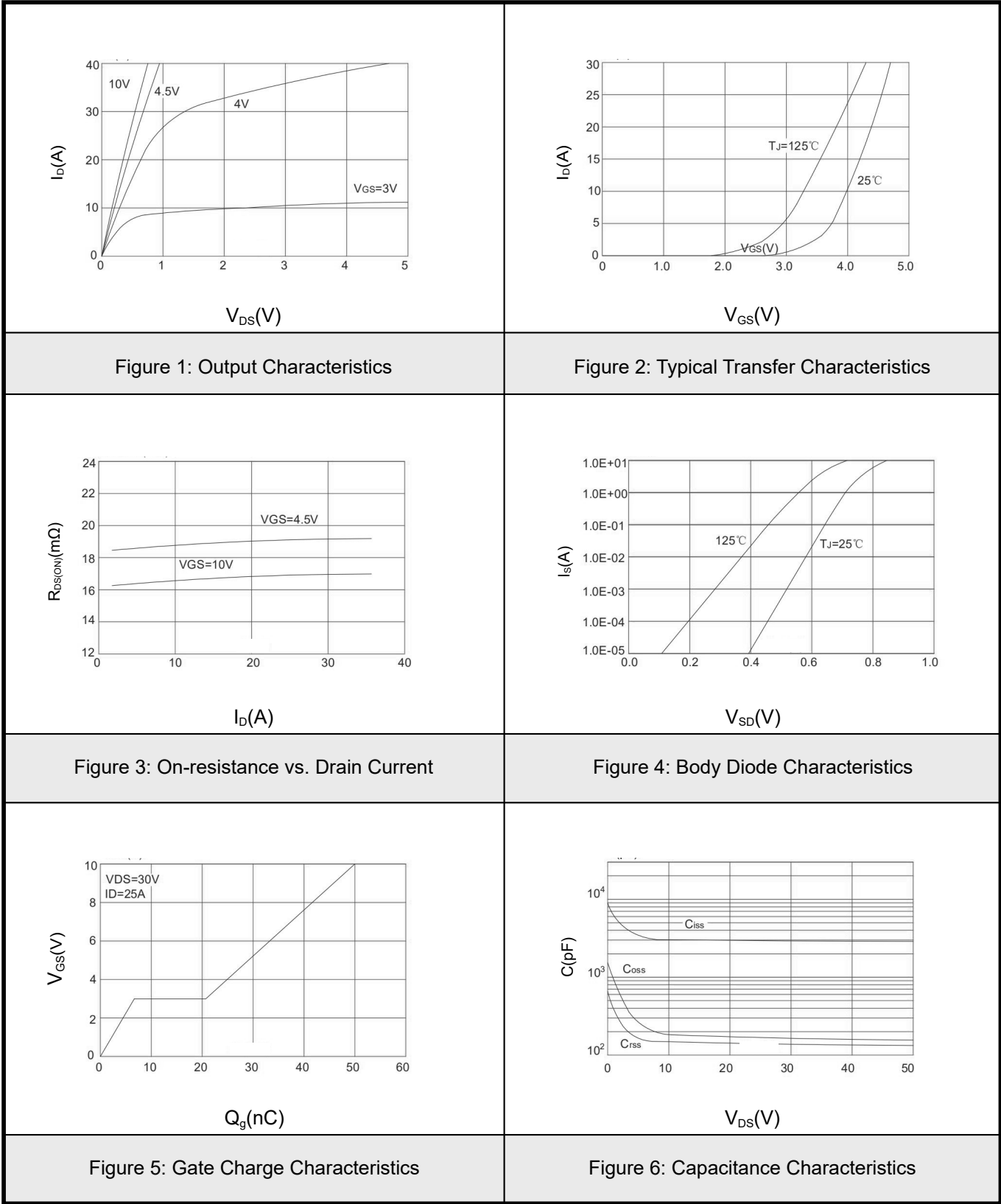
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{DS}=30A$			1.2	V
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}C, I_F=25A$		29		nS
Reverse Recovery Charge	Q_{rr}			42		uC

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, $t_s \leq 10sec$.
- 3: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4: E_{AS} condition: $L=0.5mH, V_{DD}=10V, V_G=10V, V_{GATE}=20V, Start T_J=25^{\circ}C$.

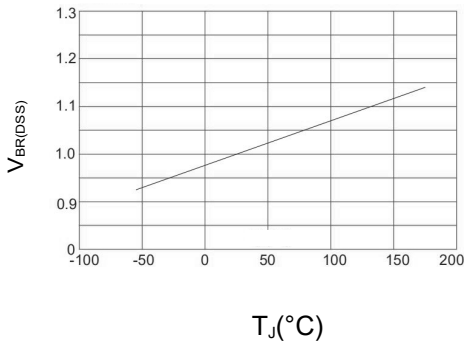
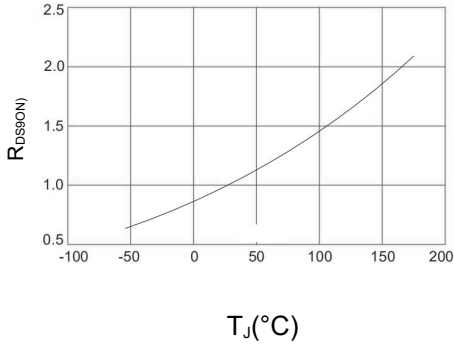
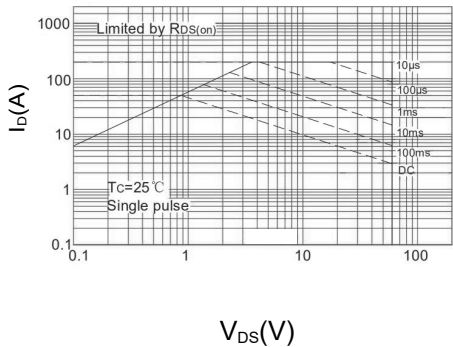
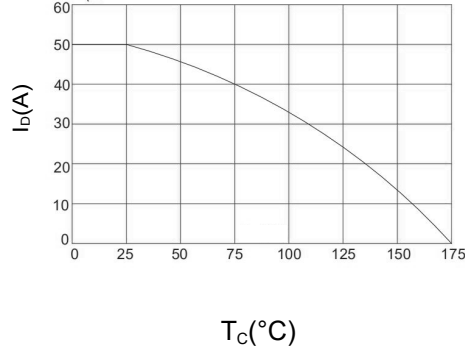
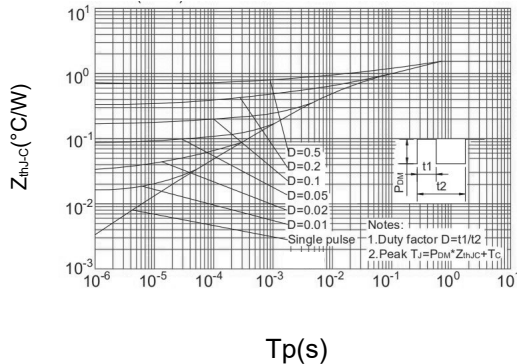


7.1 Typical Characteristics





7.2Typical Characterisitics

	
Figure 7: Normalized Breakdown Voltage vs. Junction Temperature	Figure 8: Normalized on Resistance vs Junction Temperature
	
Figure 9: Maximum Safe Operating Area	Figure 10: Maximum Continuous Drain Current vs. Case Temperature
	
Figure 11: Maximum EffectiveTransient ThermalImpedance, Junction-to-Case	

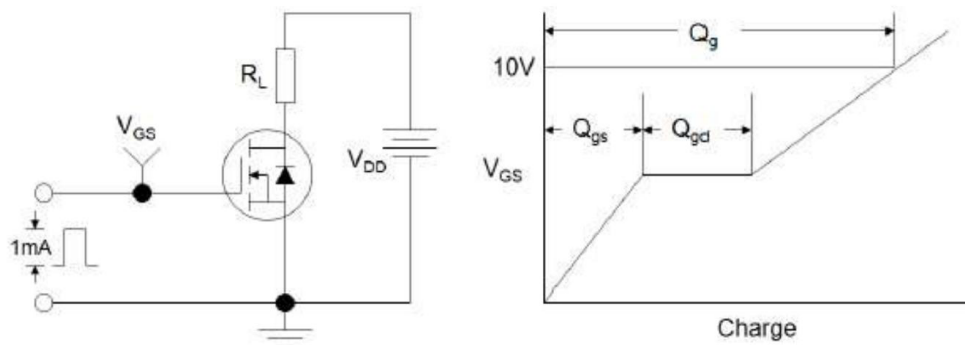


Figure1:Gate Charge Test Circuit & Waveform

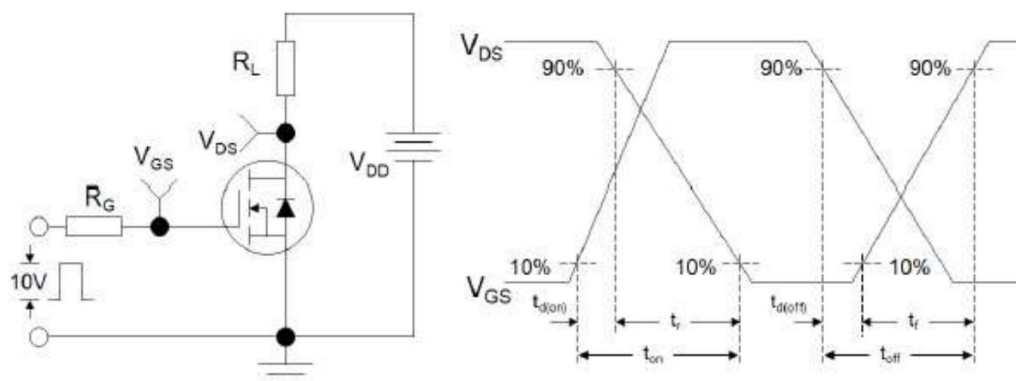


Figure 2: Resistive Switching Test Circuit & Waveforms

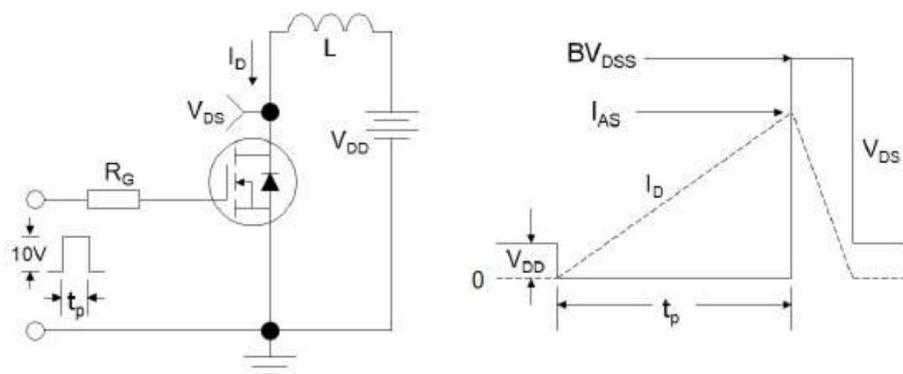
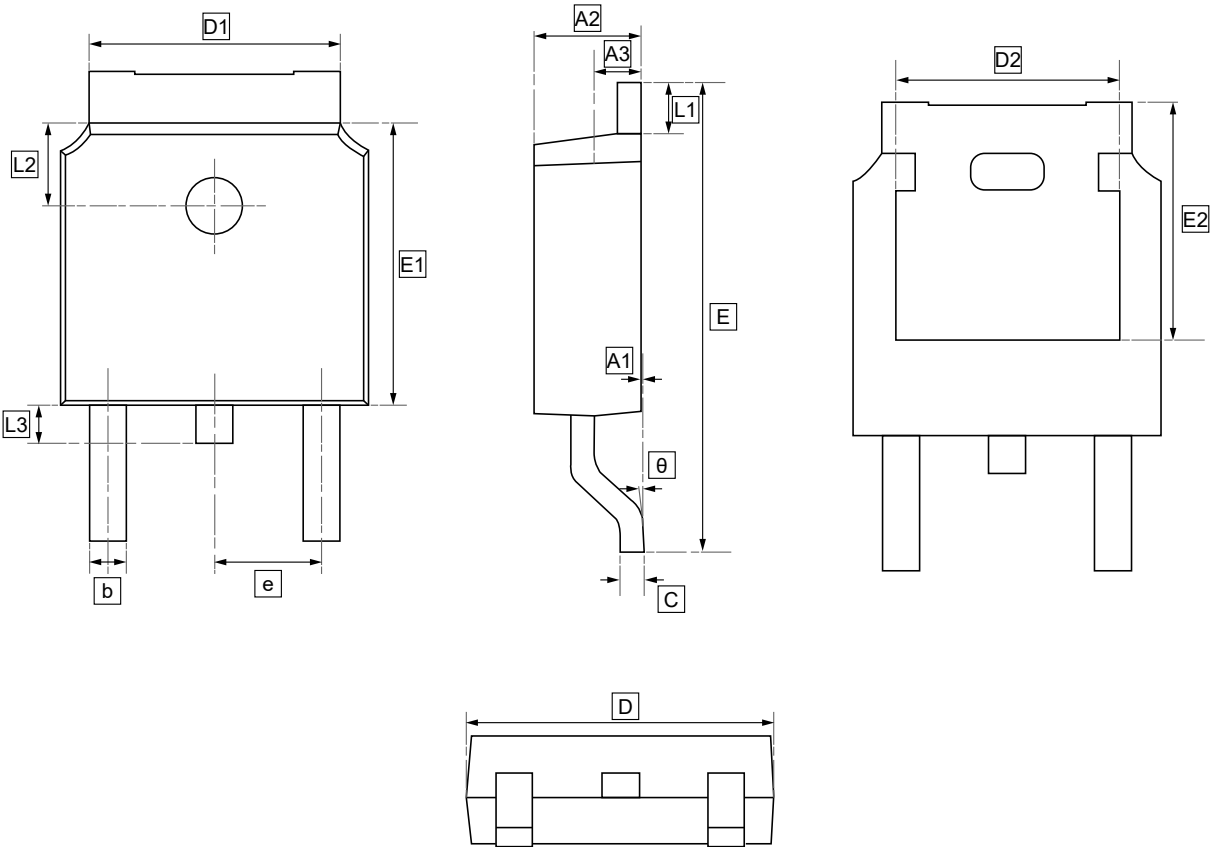


Figure 3:Unclamped inductive Switching Test Circuit & Waveforms



8.TO-252 Package Outline Dimensions

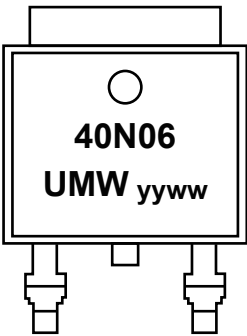


DIMENSIONS (mm are the original dimensions)

Symbol	A1	A2	A3	b	c	D	D1	D2	E	E1	E2	e	L1	L2	L3	θ
Min	0.00	2.18	0.90	0.65	0.46	6.35	4.95	4.32	9.40	5.97	5.21	2.286	0.89	1.70	0.60	0.00
Max	0.13	2.39	1.10	0.85	0.61	6.73	5.46	4.90	10.41	6.22	5.38		1.27	1.90	1.00	8.00



9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW 40N06	TO-252	2500	Tape and reel



10.Disclaimer

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